MOTOROLAC供应商 SEMICONDUCTOR TECHNICAL DATA

捷多邦,专业PCB打样工厂,24小时加急出货

by MCR12/D

Advance Information Silicon Controlled Rectifiers Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS
- High Surge Current Capability 100 Amperes
- Industry Standard TO–220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity



MCR12



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|---------------------|-------------------|-------------------------|
| Peak Repetitive Off-State Voltage (1)Peak Repetitive Reverse Voltage $(T_J = -40 \text{ to } 125^{\circ}\text{C})$ MCR12D MCR12M MCR12N | | 400 600 800 | Volts |
| On-State RMS Current (All Conduction Angles) | ^I T(RMS) | 12 | A |
| Peak Non-repetitive Surge Current (One Half Cycle, 60 Hz, T _J = 125°C) | ITSM | 100 | A A ² sec |
| Circuit Fusing Consideration (t = 8.3 ms) | l ² t | 41 | |
| Peak Gate Power (Pulse Width \leq 1.0 µs, T _C = 80°C) | PGM | 5.0 | Watts |
| Average Gate Power (t = 8.3 ms, $T_C = 80^{\circ}C$) | PG(AV) | 0.5 | Watts |
| Peak Gate Current (Pulse Width ≤ 1.0 µs, T _C = 80°C) | IGM | 2.0 | Α |
| Operating Junction Temperature Range | TJ | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

THERMAL CHARACTERISTICS

f.dzsc.com

| Thermal Resistance — Junction to Case | R _θ JC | 2.0 | °C/W |
|---|-------------------|------|------|
| — Junction to Ambient | R _θ JA | 62.5 | |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | ΤL | 260 | °C |

(1) VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

is document contains information on a new product. Specifications and information herein are subject to change without notice.



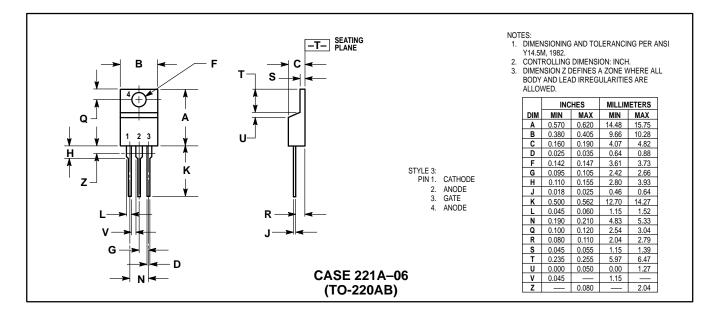
MCR12 SERIES

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|--------------------------------------|-----|------|-------------|-------|
| OFF CHARACTERISTICS | | | • | | |
| $ \begin{array}{ll} \mbox{Peak Forward Blocking Current} & T_J = 25^\circ C \\ \mbox{Peak Reverse Blocking Current} & T_J = 125^\circ C \\ \mbox{(V_{AK} = Rated V_{DRM} or V_{RRM}, Gate Open)} \end{array} $ | I _{DRM} I _{RRM} | _ | - | 0.01 2.0 | mA |
| ON CHARACTERISTICS | | | • | | • |
| Peak On-State Voltage* (I _{TM} = 24 A) | VTM | — | | 2.2 | Volts |
| Gate Trigger Current (Continuous dc) (V _D = 12 V, R _L = 100 Ω) | IGT | 2.0 | 7.0 | 20 | mA |
| Gate Trigger Voltage (Continuous dc) (V _D = 12 V, R _L = 100 Ω) | V _{GT} | 0.5 | 0.65 | 1.0 | Volts |
| Hold Current (Anode Voltage =12 V) | Iн | 4.0 | 25 | 40 | mA |
| DYNAMIC CHARACTERISTICS | | | | | |
| Critical Rate of Rise of Off–State Voltage (V_D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 25°C) | (dv/dt) | 50 | 200 | — | V/µs |

*Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

PACKAGE DIMENSIONS



Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and W are registered trademarks of Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

Literature Distribution Centers:

USA: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036.

EUROPE: Motorola Ltd.; European Literature Centre; 88 Tanners Drive, Blakelands, Milton Keynes, MK14 5BP, England.

JAPAN: Nippon Motorola Ltd.; 4-32-1, Nishi-Gotanda, Shinagawa-ku, Tokyo 141, Japan.

ASIA PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Center, No. 2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong.

